

L Number	Hits	Search Text	DB	Time stamp
1	1	438/20.ccls. and (depth near2 dop\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/18 10:02
2	1	445/\$.ccls. and (depth near2 dop\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/18 10:03
3	4	445/\$.ccls. and (depth near2 implant\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/18 10:07
4	1	(445/\$.ccls. and (depth near2 implant\$3)) and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/18 10:06
5	6195	semiconductor and (boron same (dop\$3 implant\$3) same (deep\$2 depth))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/18 10:08
6	77639	313/\$.ccls. semiconductor and (boron same (dop\$3 implant\$3) same (deep\$2 depth))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/18 10:08
7	35	313/\$.ccls. and semiconductor and (boron same (dop\$3 implant\$3) same (deep\$2 depth))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/18 10:14
8	6	(313/\$.ccls. and semiconductor and (boron same (dop\$3 implant\$3) same (deep\$2 depth))) and (ion near2 bombard\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/18 10:15
-	1	975296.apn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/18 10:01